## MBD770DWT1G, NSVMBD770DW1T1G

## Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

## Features

- Extremely Fast Switching Speed
- Low Forward Voltage
- AEC Qualified and PPAP Capable
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are $\mathrm{Pb}-$ Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS $\left(T_{J}=150^{\circ} \mathrm{C}\right.$ unless otherwise noted)

| Rating | Symbol | Value | Unit |
| :--- | :---: | :---: | :---: |
| Forward Current | $\mathrm{I}_{\mathrm{F}}$ | 100 | mA |
| Non-Repetitive Peak Forward Surge <br> Current (60 Hz Half Sine) | $\mathrm{I}_{\mathrm{FSM}}$ | 1 | A |
| Reverse Voltage | $\mathrm{V}_{\mathrm{R}}$ | 70 | V |
| Forward Power Dissipation <br> $@ \mathrm{~T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ <br> Derate above $25^{\circ} \mathrm{C}$ (Note 1) | $\mathrm{P}_{\mathrm{F}}$ | 380 <br> 3 | mW <br> $\mathrm{mW} /{ }^{\circ} \mathrm{C}$ |
| Operating Junction and Storage <br> Temperature Range | $\mathrm{T}_{\mathrm{J},} \mathrm{T}_{\mathrm{stg}}$ | -55 to +150 | ${ }^{\circ} \mathrm{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR4 @ $100 \mathrm{~mm}^{2}, 1 \mathrm{oz} \mathrm{Cu}$
*For additional information on our $\mathrm{Pb}-$ Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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## 70 VOLTS SCHOTTKY BARRIER DIODES


(Note: Microdot may be in either location)

## ORDERING INFORMATION

| Device | Package | Shipping $^{\dagger}$ |
| :---: | :---: | :---: |
| MBD770DWT1G | SOT-363 <br> (Pb-Free) | $3000 /$ <br> Tape \& Reel |
| NSVMBD770DW1T1G | SOT-363 <br> (Pb-Free) | $3000 /$ <br> Tape \& Reel |

$\dagger$ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
| :--- | :---: | :---: | :---: | :---: |
| Reverse Breakdown Voltage <br> $\left(\mathrm{I}_{\mathrm{R}}=10 \mu \mathrm{~A}\right)$ | $\mathrm{V}_{(\mathrm{BR}) \mathrm{R}}$ | 70 | - | V |
| Total Capacitance <br> $\left(\mathrm{V}_{\mathrm{R}}=20 \mathrm{~V}, \mathrm{f}=1.0 \mathrm{MHz}\right)$ | $\mathrm{C}_{\mathrm{T}}$ | - | 1.0 | pF |
| Reverse Leakage <br> $\left(\mathrm{V}_{\mathrm{R}}=35 \mathrm{~V}\right)$ | $\mathrm{I}_{\mathrm{R}}$ |  | - | 200 |
| Forward Voltage <br> $\left(\mathrm{I}_{\mathrm{F}}=1.0 \mathrm{~mA}\right)$ | $\mathrm{V}_{\mathrm{F}}$ | nA |  |  |
| Forward Voltage <br> $\left(\mathrm{I}_{\mathrm{F}}=10 \mathrm{~mA}\right)$ | $\mathrm{V}_{\mathrm{F}}$ | - | 500 | mV |



Figure 1. Typical Forward Voltage


Figure 2. Reverse Current versus Reverse Voltage


Figure 3. Typical Capacitance


RECOMMENDED SOLDERING FOOTPRINT*

*For additional information on our Pb -Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994 2. CONTROLLING DIMENSION: MILLIMETERS.
2. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
3. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF DIMENSIONS D AND E1 AT THE OUT
THE PLASTIC BODY AND DATUM H.
THE PLASTIC BODY AND DATUM H.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE DIMENSIONS b AND c APPLY TO THE FLAT SEC
LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
6. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

| DIM | MILLIMETERS |  |  | INCHES |  |  |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
|  | MIN | NOM | MAX | MIN | NOM | MAX |
| A | --- | --- | 1.10 | --- | --- | 0.043 |
| A1 | 0.00 | -- | 0.10 | 0.000 | --- | 0.004 |
| A2 | 0.70 | 0.90 | 1.00 | 0.027 | 0.035 | 0.039 |
| b | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| C | 0.08 | 0.15 | 0.22 | 0.003 | 0.006 | 0.009 |
| D | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 |
| E | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 |
| E1 | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| e | 0.65 BSC |  |  | 0.026 BSC |  |  |
| L | 0.26 | 0.36 | 0.46 | 0.010 | 0.014 | 0.018 |
| L2 | 0.15 BSC |  |  | 0.006 BSC |  |  |
| aaa | 0.15 |  |  | 0.006 |  |  |
| bbb | 0.30 |  |  | 0.012 |  |  |
| ccc | 0.10 |  |  | 0.004 |  |  |
| ddd | 0.10 |  |  | 0.004 |  |  |
|  | GENERIC |  |  |  |  |  |
|  | MARKING DIAGRAM* |  |  |  |  |  |



XXX $=$ Specific Device Code
M = Date Code*

- = Pb-Free Package
(Note: Microdot may be in either location)
*Date Code orientation and/or position may vary depending upon manufacturing location.
*This information is generic. Please refer to device data sheet for actual part marking. $\mathrm{Pb}-\mathrm{Free}$ indicator, " G " or microdot " r ", may or may not be present. Some products may not follow the Generic Marking.


## STYLES ON PAGE 2

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| DESCRIPTION: | SC-88/SC70-6/SOT-363 | PAGE 1 OF 2 |

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## SC-88/SC70-6/SOT-363

CASE 419B-02
ISSUE Y
STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 7:
PIN 1. SOURCE 2
2. DRAIN 2
3. GATE 1
4. SOURCE 1
5. DRAIN 1
6. GATE 2

STYLE 13:
PIN 1. ANODE
2. N/C
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 19:
PIN 1. IOUT
2. GND
3. GND
4. V CC
5. V EN
6. V REF
STYLE 25:
PIN 1. BASE 1
2. CATHODE
3. COLECTOR 2
4. BASE 2
5. EMITTER
6. COLLECTOR 1
STYLE 2:

CANCELLED
STYLE 8:
CANCELLED

STYLE 14:
PIN 1. VREF
2. GND
3. GND
4. IOUT
5. VEN
6. VCC

STYLE 20:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR
STYLE 26:
PIN 1. SOURCE 1
2. GATE 1
3. DRAAN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

| STYLE 3 : CANCELLED | STYLE 4: <br> PIN 1. CATHODE <br> 2. CATHODE <br> 3. COLLECTOR <br> 4. EMITTER <br> 5. BASE <br> 6. ANODE | STYLE 5: <br> PIN 1. ANODE <br> 2. ANODE <br> 3. COLLECTOR <br> 4. EMITTER <br> 5. BASE <br> 6. CATHODE | STYLE 6 : <br> PIN 1. ANODE 2 <br> 2. $\mathrm{N} / \mathrm{C}$ <br> 3. CATHODE 1 <br> 4. ANODE 1 <br> 5. N/C <br> 6. CATHODE 2 |
| :---: | :---: | :---: | :---: |
| STYLE 9: | STYLE 10: | STYLE 11: | STYLE 12: |
| PIN 1. EMITTER 2 | PIN 1. SOURCE 2 | PIN 1. CATHODE 2 | PIN 1. ANODE 2 |
| 2. EMITTER 1 | 2. SOURCE 1 | 2. CATHODE 2 | 2. ANODE 2 |
| 3. COLLECTOR 1 | 3. GATE 1 | 3. ANODE 1 | 3. CATHODE 1 |
| 4. BASE 1 | 4. DRAIN 1 | 4. CATHODE 1 | 4. ANODE 1 |
| 5. BASE 2 | 5. DRAIN 2 | 5. CATHODE 1 | 5. ANODE 1 |
| 6. COLLECTOR 2 | 6. GATE 2 | 6. ANODE 2 | 6. CATHODE 2 |
| STYLE 15: | STYLE 16: | STYLE 17: | STYLE 18: |
| PIN 1. ANODE 1 | PIN 1. BASE 1 | PIN 1. BASE 1 | PIN 1. VIN1 |
| 2. ANODE 2 | 2. EMITTER 2 | 2. EMITTER 1 | 2. VCC |
| 3. ANODE 3 | 3. COLLECTOR 2 | 3. COLLECTOR 2 | 3. VOUT2 |
| 4. CATHODE 3 | 4. BASE 2 | 4. BASE 2 | 4. VIN2 |
| 5. CATHODE 2 | 5. EMITTER 1 | 5. EMITTER 2 | 5. GND |
| 6. CATHODE 1 | 6. COLLECTOR 1 | 6. COLLECTOR 1 | 6. VOUT1 |
| STYLE 21: | STYLE 22: | STYLE 23: | STYLE 24: |
| PIN 1. ANODE 1 | PIN 1. D1 (i) | PIN 1. Vn | PIN 1. CATHODE |
| 2. $\mathrm{N} / \mathrm{C}$ | 2. GND | 2. CH 1 | 2. ANODE |
| 3. ANODE 2 | 3. D2 (i) | 3. Vp | 3. CATHODE |
| 4. CATHODE 2 | 4. D2 (c) | 4. N/C | 4. CATHODE |
| 5. N/C | 5. VBUS | 5. CH 2 | 5. CATHODE |
| 6. CATHODE 1 | 6. D1 (c) | 6. N/C | 6. CATHODE |
| STYLE 27: | STYLE 28 : | STYLE 29: | STYLE 30: |
| PIN 1. BASE 2 | PIN 1. DRAIN | PIN 1. ANODE | PIN 1. SOURCE 1 |
| 2. BASE 1 | 2. DRAIN | 2. ANODE | 2. DRAIN 2 |
| 3. COLLECTOR 1 | 3. GATE | 3. COLLECTOR | 3. DRAIN 2 |
| 4. EMITTER 1 | 4. SOURCE | 4. EMITTER | 4. SOURCE 2 |
| 5. EMITTER 2 | 5. DRAIN | 5. BASE/ANODE | 5. GATE 1 |
| 6. COLLECTOR 2 | 6. DRAIN | 6. CATHODE | 6. DRAIN 1 |

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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